

(19)



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(11)

EP 0 807 838 A1

(12)

EUROPEAN PATENT APPLICATION

(43) Date of publication:

19.11.1997 Bulletin 1997/47

(51) Int. Cl.⁶: G02B 6/42, H01S 3/025

(21) Application number: 97107800.1

(22) Date of filing: 13.05.1997

(84) Designated Contracting States:
DE FR GB

(30) Priority: 14.05.1996 JP 118645/96

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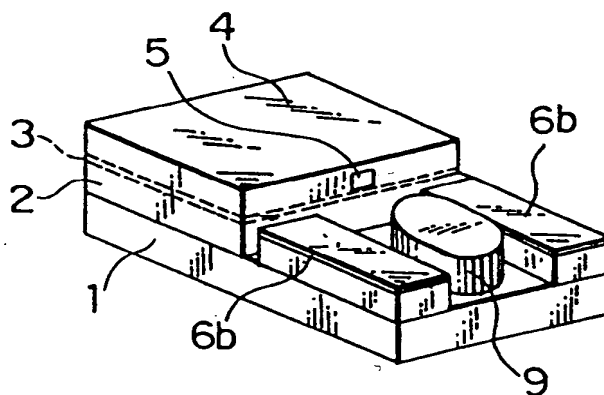
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(54) Optical waveguide coupling arrangement and fabrication process therefor

(57) An optical coupling arrangement includes an optical waveguide consisting of an optical waveguide forming layer having a lower clad layer (2,3), a core layer (5) and an upper clad layer (4). An optical element (7) is mounted on an optical element mounting portion formed by removing a part of the optical waveguide forming layer. The optical coupling circuit optically couples an end face of the exposed thin waveguide and the optical element mounted on the optical element mounting portion. In such optical coupling circuit, at least one thin film (6b) is inserted in the optical waveguide forming layer, and, in the thin film, there is a part (6a) of said thin film removed at said optical element mounting portion. By this, mass-production of the optical coupling arrangement and simplification of the fabrication process can be achieved. A reference plane in the height direction is stably formed in the wafer, and heat radiation or removing of the light emitting element can be performed.

FIG. 1A



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Description

The present invention relates generally to an optical coupling circuit for optically coupling an optical waveguide consisted of an optical waveguide forming layer having a lower clad layer, a core layer and an upper clad layer and an optical element mounted on an optical element mounting portion formed by removing a part of the optical wave guide forming layer, and a fabrication process therefor. More specifically, the invention relates to an optical coupling circuit which couples an optical waveguide and a light emitting element, a light sensing element, an optical function element or the like, and a fabrication process therefor.

In general, a device employing an optical waveguide functions not only for transmitting a light beam but also for distributing an optical power and for synthesizing and dividing wavelength of the light. Therefore, such device is essential component in future establishment of an optical communication system. However, for application in the optical communication, it is required not only to optically couple an optical waveguide of an optical device with an optical fiber, but also to optically couple the optical waveguide with an optical element, such as a light emitting element, a light sensing element or the like. Particularly, among optical communication, currently proposed optical fiber network as replacement for a subscriber network, in which electric signal cable in the current subscriber network is replaced with an optical fiber, requires to extend the optical fiber to each subscriber terminal and to optically couple the optical wave guide, the light emitting element and the light sensing element with the optical fiber line. For this purpose, it is essential to adapt the optical device for mass-production and whereby to lower a cost. In order to realize this, it has been strongly demanded down-sizing of the optical device, reduction of number of parts to be assembled, and reduction of number steps for process steps in fabrication. Among these tasks, in the optical coupling of the optical fiber with the light emitting element, a precision typically less than or equal to 1 μm is required. Therefore, large amount of period and labor are becomes inherent. This is the most important hazard for mass-production and lowering of fabrication cost. Accordingly, it has been strongly demanded to simplify optical coupling and to make respective devices adjustment-free in the coupling operation.

The inventors have already proposed a coupling method of an optical waveguide and an optical fiber (Japanese Unexamined Patent Publication (Kokai) No. Heisei 7-36949). In the proposed coupling method, adjustment-free and high precision optical coupling can be performed without requiring complicated process by forming a V-shaped groove on a waveguide substrate and setting the optical fiber with taking the V-shaped groove as a guide. However, concerning optical coupling of the light emitting element with the optical fiber or the optical waveguide, since a mode field of the light

emitting element is different from those of the optical fiber or the optical waveguide, merely less than or equal to one tenth of coupling efficiency can be obtained if the light emitting element with the optical fiber or the optical waveguide are coupled directly. For improving the coupling efficiency, there are only methods to insert a lens between the light emitting element and the optical fiber or the optical waveguide to spatially establishing optical coupling or to process the tip end of the optical fiber into hemisphere shaped configuration to provide lens effect therefor. Furthermore, in these method, since the lens is used, allowable tolerance in alignment error becomes strict to make it quite difficult to establish optical coupling in adjustment-free manner.

However, in the recent years, there has been reported a light emitting element having a mode field close to those of the optical fiber and the optical waveguide (for example, Mitomi et al. The Institute of Electronics, Information and Communication Engineers, Electronics Society Conference SC-1-2, 1995) to have about 1 to 2 dB of coupling efficiency and about ± 1 to 2 μm to have relatively wide alignment error allowable value. There has been recorded a device having a structure, in which the optical waveguide and the improved light emitting element are coupled directly each other (Yamada et al. The Institute of Electronics, Information and Communication Engineers, Electronics society Conference SC-1-11, 1995).

Also, an attempt has been made to perform optical coupling between the light emitting element and the optical waveguide (E. Friedrich et al., Journal of Light-wave Tech., Vol. 10, No. 3, pp. 336 - 339, 1992). The point of the foregoing technology will be described hereinafter. A plane to be a reference with respect to the height direction is required in order to simply and optically couple the optical waveguide and the light emitting element at high precision. In general, upon forming the optical waveguide, by surrounding the circumference of a core layer by a clad layer, absorption of the guided wave by the substrate is prevented and control of the refraction index becomes possible. At this time, a distance from the center of the waveguide passage to the surface of the substrate, namely a thickness of the lower clad layer, is required to be greater than or equal to 10 μm . However, the position of an active layer to be an optical center of a semiconductor laser or so forth employed as the light emitting element is generally 2 to 3 μm from the surface of the element. When the light emitting element is directly mounted on the substrate, coupling cannot be established at all. Therefore, it becomes necessary to provide a reference plane in the height direction of both of the light emitting element and the optical waveguide. In the method of Yamada et al., unevenness (recess and protrusion) is preliminarily formed on the surface of the substrate. After forming the lower clad layer on the substrate, planarization is performed by polishing the surface of the lower clad layer to make the protrude portion of the substrate expose. Thus, a light emitting element mounting portion is pro-

vided on the exposed portion of the substrate and a waveguide forming portion is provided at the recessed portion of the substrate where the lower clad layer is remained. In this method, since the light emitting element mounting portion is formed at the last, upon removing the waveguide forming layer located thereon, the substrate surface serves as an etching stop layer. Namely, the surface polished and planarized in the preceding step serves as the reference plane in coupling of the optical waveguide and the light emitting element. Furthermore, the exposed substrate surface serves as a heat sink to perform heat radiation of the light emitting element upon mounting the light emitting element.

On the other hand, in the method of E. Friedrich et al, upon removing the waveguide forming layer at the light emitting mounting portion, etching of a part of the mounting portion is stopped at a position where the height of the optical waveguide and the light emitting element becomes optimal. By taking this surface as the reference plane, the optimal coupling between the light emitting element and the optical waveguide is realized.

Also, in Japanese Unexamined Patent Publication No. Heisei 5-100122 by Okamura et al., a thin film layer is formed in the vicinity of the core layer. The upper surface of the thin film layer is exposed as the reference plane. By tightly fitting this reference plane with the reference plane of the guide member supporting the optical element, coupling of the optical element and the optical waveguide is established.

However, the above-mentioned prior art encounters the following problems. Namely, in the method of Yamada et al, the exposed surface of the substrate is taken as the reference plane in the height direction of the optical waveguide and the light emitting element. Therefore, high precision alignment becomes possible, and whereas polishing is inherent in fabrication process in order to provide the reference plane. This makes process complicated to cause a difficulty in performing mass-production. In case of performing mass-production, it is ideal to perform fabrication by only steps of layer formation, patterning, etching and so forth in batch process as in the semiconductor LSI process.

On the other hand, by the method of E. Friedrich et al., in order to realize high precision alignment, stopping of etching at the optimal position becomes necessary. Therefore, it becomes necessary to high precision control of etching speed of the etching device. Particularly, upon performing mass-production, since a large number of optical coupling circuits are formed on one wafer, it becomes necessary to accurately control distribution of etching speed in the wafer and distribution of layer thickness of waveguide forming layer to be etched. These problem is quite difficult to solve. Therefore, it is not practical to perform mass-production employing this method.

Also, in the method of Okamura et al, a guide member is required for the optical element to be coupled with the optical waveguide, number of necessary parts becomes large. Furthermore, when the optical element

is directly mounted on the substrate employing this method, since an under-clad is present between the substrate and the mounting position, while it is effective for coupling the element not causing heat, such as the optical fiber, the light sensing element and the like and the optical waveguide, it is not effective for coupling the light emitting element which generates a heat, as sufficient heat radiation cannot be performed.

In order to enable mass-production of the optical coupling circuit for the optical waveguide and the light emitting element toward the future, it is essential to enable fabrication in batch simple process, to stably form the reference plane in the height direction in the wafer, and to permit sufficient heat radiation of the light emitting element.

It is therefore an object of the present invention to provide an optical coupling circuit and a fabrication process thereof, which can stably form a reference plane in a height direction in a wafer and can perform sufficient heat radiation of a light emitting element.

Another object of the present invention is to provide an optical coupling circuit which can be fabricated by a series of simple process steps and can be fabricated by mass-production.

An optical coupling circuit for optically coupling an optical element according to the present invention comprises an optical waveguide formed by patterning an optical waveguide forming layer having a lower clad layer, a core layer and an upper clad layer; an optical element mounting portion formed by removing a part of said optical waveguide forming layer; and at least one thin film inserted in said optical waveguide forming layer, a part of said thin film being removed at said optical element mounting portion.

A fabrication process of an optical coupling circuit for optically coupling an optical element according to the present invention comprises the steps of: forming an optical waveguide forming layer having a lower clad layer, a core layer and an upper clad layer, with inserting at least one thin film in said optical waveguide forming layer and removing a part of said thin film at an optical element mounting portion; removing a part of said optical waveguide forming layer at said optical element mounting portion to constitute an optical waveguide and said optical element mounting portion and expose the surface of said thin film; and exposing a part of the surface of the substrate where said thin film is removed.

According to the present invention, it becomes not at all necessary to control the etching rate with high precision and control a layer thickness distribution at high precision with the mask of the optical element mounting portion. Namely, even when the mask is exposed by etching, by employing a layer having quite low etching rate relative to the waveguide forming layer as a masking material, the reference plane in the height direction can be stably formed. Furthermore, since a part of the mask of the optical element mounting portion can be removed, the waveguide forming layer at this portion is removed to expose the substrate. Thus, exposed sub-

strate surface and the optical element are contacted via a material having high electrical or thermal conductivity, and can be formed as a heat sink. Furthermore, in order to realize the shown method, it is only required to insert the thin film between the optical waveguide forming layers. It becomes possible to form in normal layer deposition and patterning process, and thus is optimal for mass-production.

The present invention will be understood more fully from the detailed description given hereinafter and from the accompanying drawings of the preferred embodiment of the present invention, which, however, should not be taken to be limitative to be present invention, but are for explanation and understanding only.

In the drawings:

Figs. 1A and 1B are respective perspective view and section showing an optical element of an optical coupling circuit of the first embodiment according to the present invention, in a condition before mounting;

Figs. 2A and 2B are respective perspective view and section showing an optical element of an optical coupling circuit of the first embodiment according to the present invention, in a condition after mounting the optical element;

Figs. 3A to 3E are perspective views showing a fabrication process of the optical coupling circuit of the first embodiment according to the present invention in sequential order;

Figs. 4A to 4C are plan view of the optical coupling circuit of the second to fourth embodiments according to the present invention;

Fig. 5 is a section of the optical coupling circuit of the fifth embodiment according to the invention; and

Figs. 6A and 6B are respectively perspective view and section showing an optical coupling circuit of the sixth embodiment according to the present invention.

The present invention will be discussed hereinafter in detail in terms of the preferred embodiment of the present invention with reference to the accompanying drawings. In the following description, numerous specific details are set forth in order to provide a thorough understanding of the present invention. It will be obvious, however, to those skilled in the art that the present invention may be practiced without these specific details. In other instance, well-known structures are not shown in detail in order to avoid unnecessary obscure the present invention.

Figs. 1A and 1B are respective perspective view and section showing an optical element of an optical coupling circuit of the first embodiment according to the present invention, in a condition before mounting, Figs. 2A and 2B are respective perspective view and section showing an optical element of an optical coupling circuit of the first embodiment according to the present inven-

tion, in a condition after mounting, and Figs. 3A to 3E are perspective views showing a fabrication steps of the optical coupling circuit of the first embodiment according to the invention in sequential order.

In order to form a mask for stopping etching between lower clad layers in the shown embodiment, the lower clad layers are deposited through separate two disposition processes. At first, as shown in Fig. 3A, after deposition of a first lower clad layer 2 on a substrate 1, a thin film 6 to be a mask for stopping etching is locally formed at one end portion of the lower clad layer 2. Subsequently, in the optical element mounting portion, a central portion of the thin film 6 is removed. In Fig. 3B, an optical element mounting portion 6a where the thin film 6 is removed and a portion 6b where the thin film 6 is remained, are illustrated.

Subsequently, as shown in Fig. 3C, over the entire surface, a second lower clad layer 3 and a core layer 5 are formed sequentially. Here, in order to accurately determine the position in the height direction, it becomes necessary to determine a layer thickness to be preliminarily deposited. A distance from the surface of the optical element 7 (see Figs. 2A and 2B) to be mounted, to the center of the active layer 8 to be the optical center is assumed to be d_1 , the layer thickness of the core layer 5 is assumed to be d_2 , then the necessary layer thickness of the second lower clad layer 3 is determined by $(d_1 - d_2/2)$. As one example, assuming that the layer thickness d_2 of the core layer 6 is 6 μm , a distance d_1 from the surface of the optical element 7 to the center of an active layer 8 to be the optical center is 4 μm , a layer thickness required for the second lower clad layer 3 becomes 1 μm .

At this time, the layer thickness of the first lower clad layer 2 is required to be in a thickness in combination with the second lower clad layer 3, sufficient to prevent absorption of a guided light by the substrate. It is not required a high precision of the layer thickness of the first lower clad layer 2. A height from the second lower clad layer 3 to the center of the core layer 5 is 4 μm , for example. Even when the fluctuation in the wafer surface in layer thickness in layer formation, is in the extent of $\pm 10\%$, the fluctuation of the height becomes about $\pm 0.4 \mu\text{m}$. This is sufficiently high precision to perform high efficiency optical coupling.

Next, as shown in Fig. 3D, the core layer 5 is etched to be patterned in a configuration of a waveguide. After performing etching, an upper clad layer 4 is deposited. Concerning the upper clad layer 4, if sufficiently large thickness is provided, accuracy of layer thickness becomes unnecessary at all.

Thereafter, as shown in Fig. 3E, etching of the optical waveguide forming layer of the portion mounting the optical element 7 is performed.

At this time, etching of the portion 6a where the thin film 6 of the optical element mounting portion is removed, is progressed up to the surface 13 of the substrate. Etching is stopped when the surface 13 of the substrate is exposed. On the other hand, the portion 6b

where the thin film 6 as the optical element mounting portion is remained, stops etching reaching thereto. Accordingly, the exposed surface 13 of the substrate is the reference plane in the height direction upon mounting of the optical element. In order to mount the optical element on the surface of the portion 6b where the exposed thin film 6 is remained, a relationship in position between the portion 6a where the thin film 6 is removed in the optical element mounting portion and the portion 6b where the thin film 6 is remained is established as in the second to fourth embodiment shown in Figs. 4A, 4B and 4C, to make it possible to stably mount the optical element.

Fig. 4A shows the second embodiment, in which the portions 6b where the thin film 6 is remained, are formed at four corners in a forming region of the thin film 6. Fig. 4B shows the third embodiment, in which the portions 6b where the thin film 6 is remained, are formed along four edges in a manner surrounding the portion 6a where the thin film 6 is removed. In Fig. 4C, a pair of portions 6b where the thin film 6 is remained, are located in opposition across the portion 6a where the thin film 6 is removed.

In Fig. 3E, upon performing etching, it is desirable to simply the process by simultaneously forming the optical element 7 and the end surface portion of the waveguide to be optically coupled thereto. The end surface portion of the waveguide is required sufficient flatness and verticality for obtaining good coupling efficiency. Therefore, it is desirable to form it by dry etching, such as reactive ion etching (RIE), an ion beam etching (IBE), a reactive ion beam etching (RIBE). However, even when the dry etching is not employed, it is also possible to perform wet etching instead of dry etching, and subsequently curve a groove on the end face portion by mechanical process, such as that employing dicing saw or so forth.

As pointed out in the description of the prior art, among optical elements, the semiconductor laser to be typically employed as the light emitting element, has large heat generation amount. Therefore, it becomes necessary to make it contact with a material called as a heat sink and having large thermal capacity to remove the heat of the semiconductor layer. As the material for the heat sink, Si, BN and the like may be used. However, it is preferred to directly use Si which is typically used as a material of the substrate.

In the shown embodiment, by providing the portion 6a where the thin film 6 is removed, the Si substrate exposed at this portion is contacted with the mounted optical element via a material having generally high thermal conductivity, to enable heat irradiation of the optical element. Typically, as a material having high thermal conductivity, high electric conductivity and mechanical bonding function is AuSn solder or the like. On the exposed surface portion of the substrate, a solder bump 9 having sufficient thickness is formed with AuSn solder or the like. Then, by contacting the optical element 7 to be mounted with the solder bump 9, suffi-

cient heat radiation effect through the solder bump can be attained. Here, alignment in the height direction can be done with taking the portion 6b as the etching stopping mask. Therefore, high accuracy alignment can be maintained irrespective of the height of the solder bump.

Here, for the portion 6b serving as the etching stop mask, a characteristics is required to be etched little even when etching of the first lower clad layer 2 is performed. In general, the layer thickness of the lower clad layer is required to be greater than or equal to 10 μm . Therefore, in order to achieve $\pm 1 \mu\text{m}$ of precision required for maintaining high precision alignment in the height direction, it becomes necessary that the thickness of the portion serving as the etching stopping mask to be less than or equal to 1 μm . Therefore, an etching rate ratio (generally called as selection ratio) between the portion to be the etching stopping mask and the lower clad layer has to be greater than or equal to 10 times. As a material to achieve the selection ratio of greater than or equal to 10 times, a metal such as polycrystalline Si, Cr, Au, Pt and the like, a silicide, such as WSi, MoSi, or the like may be effective. As a characteristics required for the material of the mask, in addition to the characteristics to provide high selection ratio, it is also required that the layer quality should not be degraded upon formation of the second clad layer, the core layer and the upper clad layer. In general, as the material for forming the waveguide, there are quartz layer or Si_3N_4 which can be varied the refraction index by doping P, Ge, B, Ti or the like. The quartz layer which is particularly frequently used can be deposited by a normal pressure CVD method, a low pressure CVD method, a plasma CVD method, a frame deposition method and so forth. In order to prevent degradation of layer quality of the mask, it is desirable to form in low temperature as low as possible.

In the foregoing method, high precision alignment in the height direction can be simply realized, for simple mounting of the optical element, it is desirable to perform alignment in the transverse direction (in-plane direction of the substrate). As a method for realizing this, there is an index alignment method employing an image recognition. This method enables precise alignment with the optical waveguide by image recognition of a marker by providing the marker at the position on the substrate and also providing a marker on the optical element. By combining this method, upon performing optical coupling of the optical waveguide and the optical element, passive alignment can be realized by performing mounting without monitoring, and thus is optimal for mass-production.

It should be noted that while the foregoing embodiment has been discussed with respect to the case where the position of the surface of the optical element is located between the lower clad layers upon mounting. In the case where the position of the active layer of the optical element is located at the position further close position from the surface of the optical element, the surface of the optical element may located between the

core layers upon mounting. In such case, as in the fifth embodiment shown in Fig. 5, the core layer 5 is formed on the lower clad layer 10 as separately deposited first core layer 11a and a second core layer 11b, and between these, an etching stop mask 6b may be formed.

Furthermore, in the recent years, there is a case where the only a portion of the active layer 8 is bulged in trapezoidal form beyond the surface of the optical element 7 as in the sixth embodiment shown in Fig. 6A. In this case, the surface of the optical element may be located between the upper clad layers upon mounting. In this case, the upper clad layer 4 is deposited as separated the first upper clad layer 12a and the second upper clad layer 12b, and between these first and second upper clad layers 12a and 12b, the etching stopping mask 6b may be formed. At this time, the etching stopping mask has to be preliminarily removed at a portion located at the active layer among the portion mounting the optical element.

As set forth above, the present invention constructs with the optical waveguide consisted of the optical waveguide forming layer of the lower clad layer, the core layer and the upper clad layer, removing a part of the optical waveguide forming layer, and optically coupling the optical element to the end face of the waveguide. In the optical waveguide forming layer, at least one thin film is inserted to have a structure where a part of the thin film at the optical element mounting portion is removed. The remained thin film portion serves as the etching stopping mask of the optical element mounting portion upon formation of the end face to be coupled with the optical element of the optical waveguide and can be used as a reference surface for alignment in the height direction. Furthermore, at the portion where the thin film is removed, the waveguide forming layer is removed by etching and the surface of the substrate is exposed. Therefore, via a material having high thermal conductivity, the substrate as the heat sink and the optical element are contacted. Thus, the position of the optical waveguide and the optical element in the height direction can be controlled with high precision, and heat radiation for the optical element which generates a heat, can be performed satisfactorily. Thus, stable mounting of the light emitting element becomes possible. Furthermore, little fluctuation of alignment error in the wafer should be caused, it is significantly effective in mass-production of the optical coupling circuit.

While the foregoing embodiment is mainly directed to coupling between the light emitting element or light sensing element and the optical waveguide, application of the present invention should not be limited to the light emitting element or the light sensing element. As the optical waveguide device which is practiced other than the quartz waveguide, is LiNbO₃ substrate. This material has electrooptic effect and piezoelectric effect, a light modulator, an optical switch and so forth may be applied as a function device. While the quartz waveguide has superior characteristics as the optical

waveguide, but has no function which is achieved by the LiNbO₃. Therefore, it is quite attractive to use these in combination. Since the optical waveguide formed in the LiNbO₃ substrate is generally position in the vicinity of the surface of substrate, it is obvious to be easily coupled by the present invention similarly to the light emitting element, light sensing element and so forth.

Claims

1. An optical coupling circuit for optically coupling an optical element (7) comprising:

an optical waveguide formed by patterning an optical waveguide forming layer having a lower clad layer (2,3), a core layer (5) and an upper clad layer (4);

an optical element mounting portion formed by removing a part of said optical waveguide forming layer; and

at least one thin film (6b) inserted in said optical waveguide forming layer, a part of said thin film being removed at said optical element mounting portion.

2. An optical coupling circuit optically coupling an optical element as set forth in claim 1, wherein said optical waveguide forming layer is completely removed to expose a substrate (1), on which said optical waveguide forming layer is formed, at a portion where the thin film is removed at said optical element mounting portion.
3. An optical coupling circuit optically coupling an optical element as set forth in claim 2, which includes a member having a high electric conductivity or thermal conductivity contacting with the optical element mounted on the exposed surface of said substrate.
4. A fabrication process of an optical coupling circuit for optically coupling an optical element comprising the steps of:

forming an optical waveguide forming layer having a lower clad layer (2,3), a core layer (5) and an upper clad layer (4) on a substrate (1), with inserting at least one thin film (6b) in said optical waveguide forming layer and removing a part of said thin film at an optical element mounting portion;

removing a part of said optical waveguide forming layer at said optical element mounting portion to constitute an optical waveguide and said optical element mounting portion and expose the surface of said thin film; and

exposing a part of the surface of the substrate where said thin film is removed.

5. A fabrication process of an optical coupling circuit

as set forth in claim 4, wherein, in a step of removing a part of said optical waveguide forming layer, an etching rate of said thin film (6b) is lower than or equal to one tenth of the etching rate of said waveguide forming layer.

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FIG. 1A

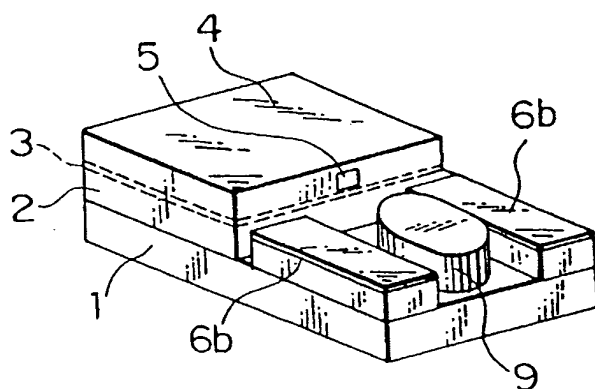


FIG. 1B

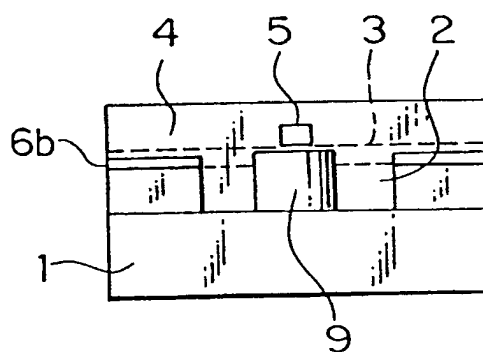


FIG. 2A

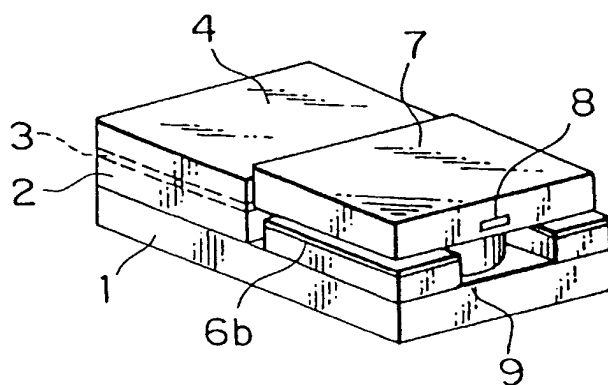


FIG. 2B

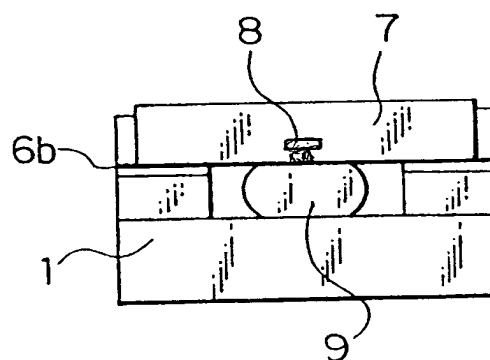


FIG. 3A

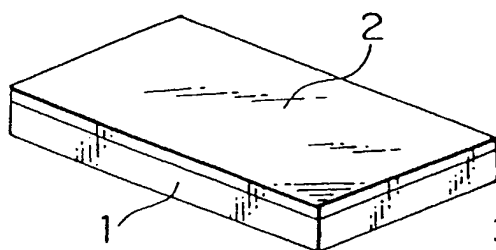


FIG. 3B

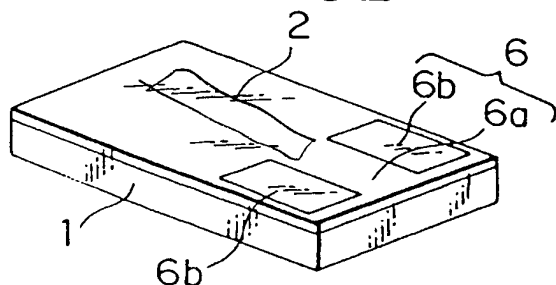


FIG. 3C

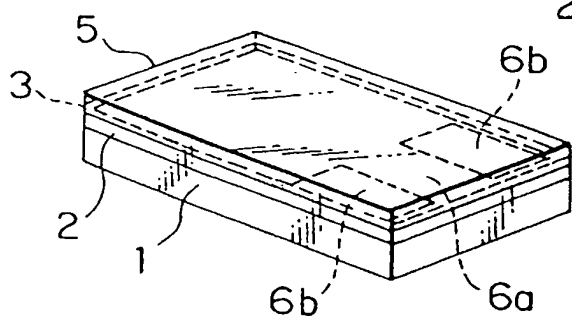


FIG. 3D

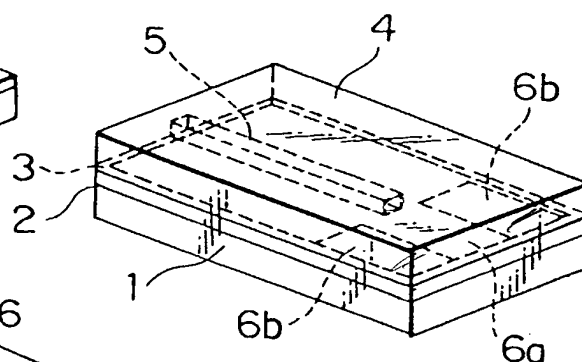


FIG. 3E

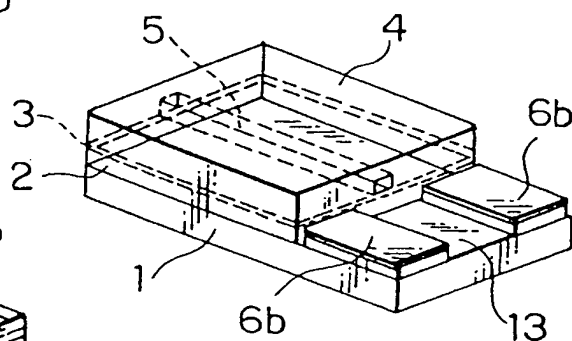


FIG. 4A FIG. 4B FIG. 4C

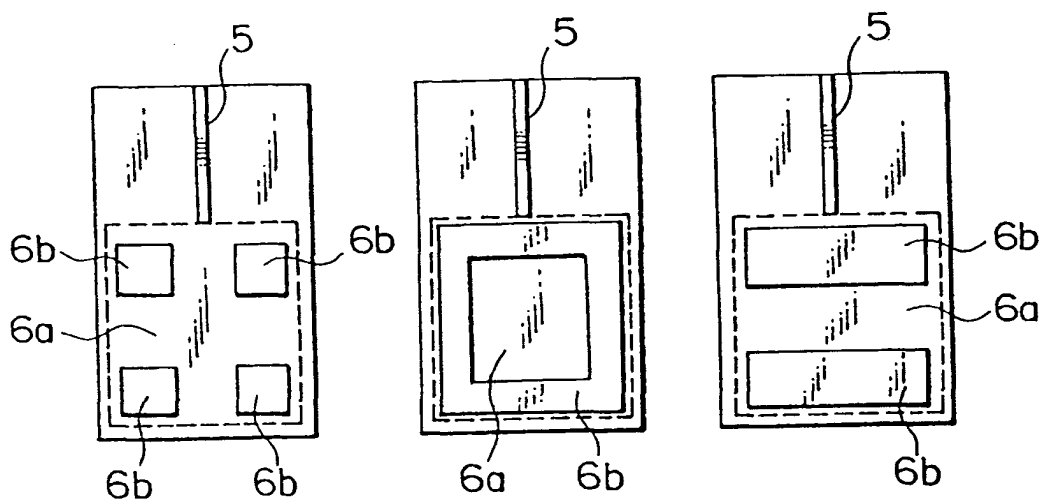


FIG. 5

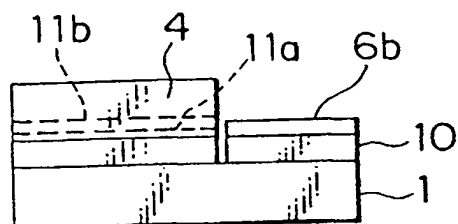


FIG. 6A

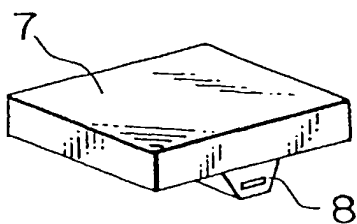
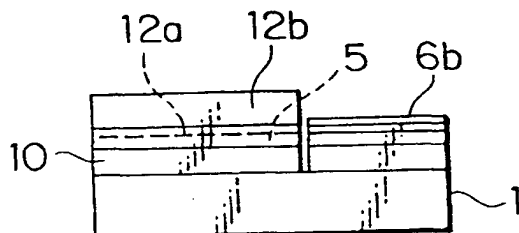


FIG. 6B





European Patent
Office

EUROPEAN SEARCH REPORT

Application Number
EP 97 10 7800

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.6)
X	DATABASE WPI Section Ch, Week 9434 Derwent Publications Ltd., London, GB; Class L03, AN 94-273815 XP002037257 & JP 06 201 930 A (NIPPON TELEGRAPH & TELEPHONE CORP), 22 July 1994 * abstract; figures 1,2,4,9 *	1,2,4,5	G02B6/42 H01S3/025
Y	---	3	
D,Y	JOURNAL OF LIGHTWAVE TECHNOLOGY, vol. 10, no. 3, 1 March 1992, pages 336-340, XP000272892 FRIEDRICH E E L ET AL: "HYBRID INTEGRATION OF SEMICONDUCTOR LASERS WITH SI-BASED SINGLE-MODE RIDGE WAVEGUIDES" Sections IV and VI	3	
P,X	EP 0 716 321 A (ALCATEL NV) 12 June 1996 * claim 5; figures 5-10 *	1	
D,A	PATENT ABSTRACTS OF JAPAN vol. 017, no. 448 (P-1594), 17 August 1993 & JP 05 100122 A (FUJITSU LTD), 23 April 1993, * abstract *	1-5	TECHNICAL FIELDS SEARCHED (Int.Cl.6) G02B H01S
The present search report has been drawn up for all claims			
Place of search MUNICH		Date of completion of the search 8 August 1997	Examiner Lord, R
<p>CATEGORY OF CITED DOCUMENTS</p> <p>X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document</p> <p>T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document</p>			

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